

ABSTRACT OF THE DISCLOSURE

There is disclosed a semiconductor device comprising a capacitor comprising a lower electrode provided above a substrate, a capacitor insulating film selectively provided on the lower electrode, and an upper electrode selectively provided above the lower electrode so that the capacitor insulating film can be interposed between the upper and lower electrodes, an electrode protection film formed of oxide conductors containing at least one of metal elements such as Sr, Ti, Ru, Ir and Pt, and provided on the upper electrode, an interlayer insulating film provided on the electrode protection film, an upper layer interconnect wire for the lower electrode provided on the interlayer insulating film, and electrically connected to the lower electrode, and an upper layer interconnect wire for the upper electrode provided on the interlayer insulating film, and electrically connected to the upper electrode.